

101 677433

I hereby certify that this paper (along with any paper referred to as being attached and enclosed) is being deposited with the U.S. Postal Service on the date shown below with sufficient postage as First Class Mail, in an envelope addressed to:  
Attention: Certificate of Correction Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Dated: January 8, 2007

Signature:

  
(Richard H. Anderson)Docket No.: 28569/38510  
(PATENT)**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Letters Patent of:  
Fang et al.

Patent No.: 7,087,529

Issued: August 8, 2006

For: CHEMICAL-MECHANICAL POLISHING  
(CMP) SLURRY AND METHOD OF  
PLANARIZING SURFACES

**Certificate**  
JAN 12 2007  
**of Correction**

**REQUEST FOR CERTIFICATE OF CORRECTION**  
**PURSUANT TO 37 CFR 1.322**

Attention: Certificate of Correction Branch  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted typographical errors which should be corrected.

**In the Abstract:**

At Section (57), please delete "A chemical-mechanical abrasive composition for use in semiconductor processing uses abrasive particles having a non-spherical morphology." and insert -- Compositions and methods for planarizing or polishing a surface, particularly a semiconductor wafer surface. The polishing compositions described herein comprise (a) a liquid carrier; (b) purified clay; and optional additives, such as (c) a chemical accelerator; and (d) a complexing or coupling agent capable of chemically or ionically complexing with, or coupling to, the metal and/or insulating material removed during the polishing process. The complexing or coupling agent carries away

JAN 16 2007

the removed metal and/or silicon dioxide insulator particles, during polishing, to prevent the separated particles from returning to the surface from which they were removed. Also disclosed are methods of planarizing or polishing a surface comprising contacting the surface with the compositions.

The errors in the abstract were not found in the application papers as filed by applicant, since the abstract was mailed January 15, 2004, in response to the Notice to File Corrected Application Papers.

The errors now sought to be corrected do not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentee respectfully solicits the granting of the requested Certificate of Correction.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 13-2855, under Order No. 28569/38510. A duplicate copy of this paper is enclosed.

Dated: January 8, 2007

Respectfully submitted,

By Richard H. Anderson

Richard H. Anderson

Registration No.: 26,526

MARSHALL, GERSTEIN & BORUN LLP

233 S. Wacker Drive, Suite 6300

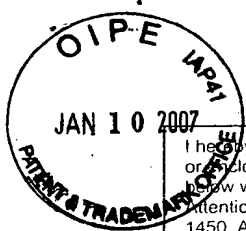
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JAN 16 2007



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**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

Page 1 of 1

PATENT NO. : 7,087,529  
APPLICATION NO. : 10/677,433  
ISSUE DATE : August 8, 2006  
INVENTOR(S) : Fang et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Title Page:

At Section (57), please insert "A chemical-mechanical abrasive composition for use in semiconductor processing uses abrasive particles having a non-spherical morphology." and insert – Compositions and methods for planarizing or polishing a surface, particularly a semiconductor wafer surface. The polishing compositions described herein comprise (a) a liquid carrier; (b) purified clay; and optional additives, such as (c) a chemical accelerator; and (d) a complexing or coupling agent capable of chemically or ionically complexing with, or coupling to, the metal and/or insulating material removed during the polishing process. The complexing or coupling agent carries away the removed metal and/or silicon dioxide insulator particles, during polishing, to prevent the separated particles from returning to the surface from which they were removed. Also disclosed are methods of planarizing or polishing a surface comprising contacting the surface with the compositions.

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 (Richard H. Anderson)

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